

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A memory cell comprising:

a first electrode ~~deposited on~~ over a substrate body;

a second electrode, wherein the first electrode and the second electrode provide electrical access to ~~the~~ a memory cell body;

Uet ~~a first layer of a silver chalcogenide layer~~ disposed between the first electrode and the second electrode, where the ^{*silver chalcogenide*} ~~first~~ layer forms a first portion of a the memory cell body; and

~~a second layer of a rigid chalcogenide glass layer, that forms a second portion of the memory cell body, wherein the second rigid chalcogenide glass layer is also disposed between the first electrode and the second electrode and forms a second portion of the memory cell body, wherein the rigid chalcogenide glass permits comprises silver chalcogenide material from said silver chalcogenide layer in an amount such that a conductive pathway to can form between the first electrode and the second electrode in said rigid chalcogenide glass layer in response to an electric potential applied between the first electrode and the second electrode.~~

2. (Currently Amended) The memory cell ~~as defined in~~ of Claim 1, wherein ~~the first layer of the silver chalcogenide layer~~ is formed directly on the first electrode.